

IXTP44N10T-VB Datasheet

N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY

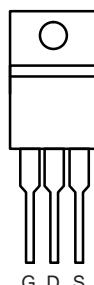
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
100	0.017 at $V_{GS} = 10$ V	70 ^a

FEATURES

- Trench Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- 100 % R_g Tested



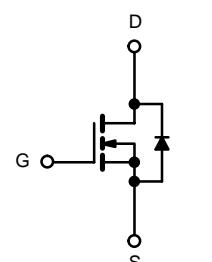
TO-220AB



Top View

APPLICATIONS

- Isolated DC/DC Converters



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	70 ^a	A
		35 ^a	
Pulsed Drain Current	I_{DM}	145	A
Avalanche Current	I_{AS}	31	
Single Pulse Avalanche Energy ^b	E_{AS}	60	mJ
Maximum Power Dissipation ^b	P_D	355 ^c	W
		3.35	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.4	

Notes:

a. Package limited.

b. Duty cycle ≤ 1 %.

c. See SOA curve for voltage derating.

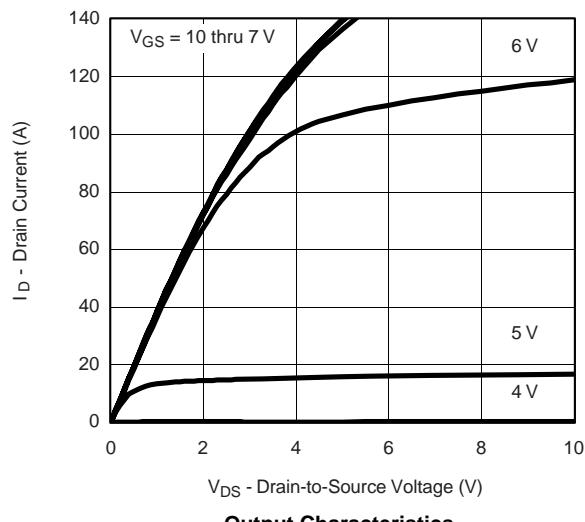
d. When Mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{DS}} = 0 \text{ V}, I_{\text{D}} = 250 \mu\text{A}$	100			V
Gate-Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250 \mu\text{A}$	2		4	
Gate-Body Leakage	I_{GSS}	$V_{\text{DS}} = 0 \text{ V}, V_{\text{GS}} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 100 \text{ V}, V_{\text{GS}} = 0 \text{ V}$			1	μA
		$V_{\text{DS}} = 100 \text{ V}, V_{\text{GS}} = 0 \text{ V}, T_J = 125^\circ\text{C}$			50	
		$V_{\text{DS}} = 100 \text{ V}, V_{\text{GS}} = 0 \text{ V}, T_J = 175^\circ\text{C}$			250	
On-State Drain Current ^a	$I_{\text{D}(\text{on})}$	$V_{\text{DS}} \geq 5 \text{ V}, V_{\text{GS}} = 10 \text{ V}$	120			A
Drain-Source On-State Resistance ^a	$r_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}, I_{\text{D}} = 30 \text{ A}$		0.017		Ω
		$V_{\text{GS}} = 10 \text{ V}, I_{\text{D}} = 30 \text{ A}, T_J = 125^\circ\text{C}$		0.023		
		$V_{\text{GS}} = 10 \text{ V}, I_{\text{D}} = 30 \text{ A}, T_J = 175^\circ\text{C}$		0.037		
Forward Transconductance ^a	g_{fs}	$V_{\text{DS}} = 15 \text{ V}, I_{\text{D}} = 30 \text{ A}$	25			S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 25 \text{ V}, f = 1 \text{ MHz}$		1800		pF
Output Capacitance	C_{oss}			210		
Reverse Transfer Capacitance	C_{rss}			110		
Total Gate Charge ^c	Q_{g}	$V_{\text{DS}} = 100 \text{ V}, V_{\text{GS}} = 10 \text{ V}, I_{\text{D}} = 58 \text{ A}$		90		nC
Gate-Source Charge ^c	Q_{gs}			23		
Gate-Drain Charge ^c	Q_{gd}			34		
Gate Resistance	R_{g}		0.5	1.3	3.1	Ω
Turn-On Delay Time ^c	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 100 \text{ V}, R_{\text{L}} = 1.5 \Omega$ $I_{\text{D}} \equiv 58 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, R_{\text{g}} = 2.5 \Omega$		24	35	ns
Rise Time ^c	t_{r}			220	330	
Turn-Off Delay Time ^c	$t_{\text{d}(\text{off})}$			45	70	
Fall Time ^c	t_{f}			200	300	
Source-Drain Diode Ratings and Characteristics $T_C = 25^\circ\text{C}^b$						
Continuous Current	I_{S}				70	A
Pulsed Current	I_{SM}			115		
Forward Voltage ^a	V_{SD}	$I_{\text{F}} = 58 \text{ A}, V_{\text{GS}} = 0 \text{ V}$		1.0	1.5	V
Reverse Recovery Time	t_{rr}	$I_{\text{F}} = 30 \text{ A}, \text{di/dt} = 100 \text{ A}/\mu\text{s}$		130	200	ns
Peak Reverse Recovery Current	$I_{\text{RM}(\text{REC})}$			8	12	A
Reverse Recovery Charge	Q_{rr}			0.52	1.2	μC

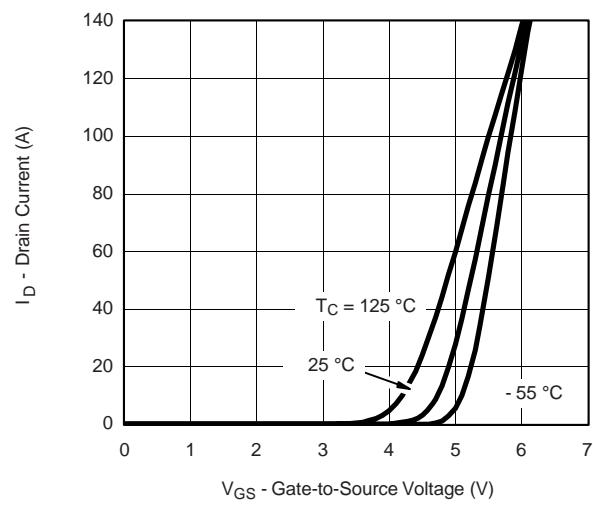
Notes:

- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

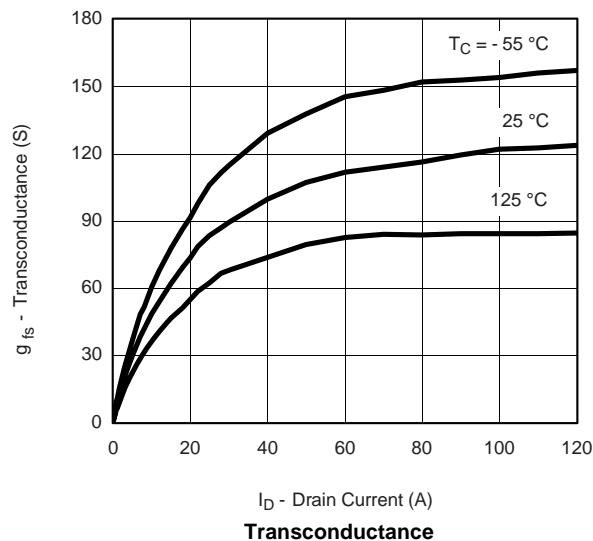
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


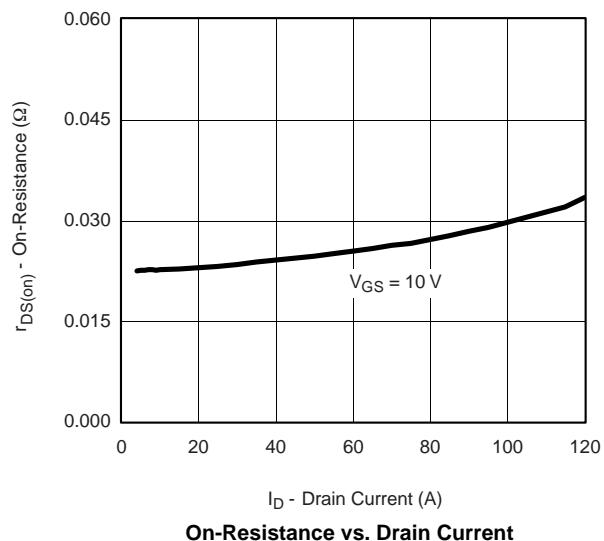
Output Characteristics



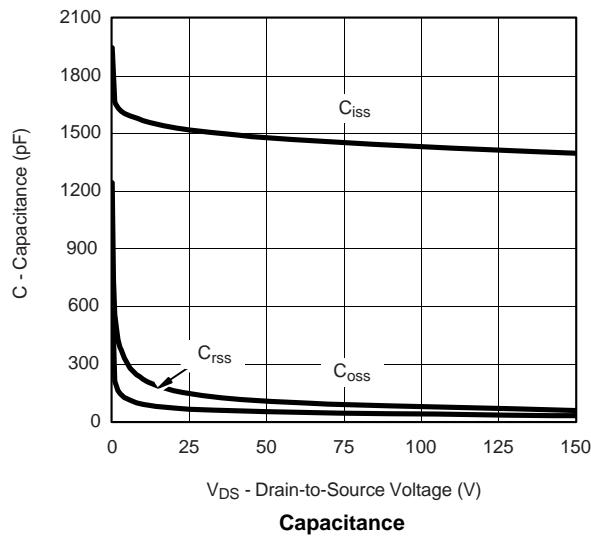
Transfer Characteristics



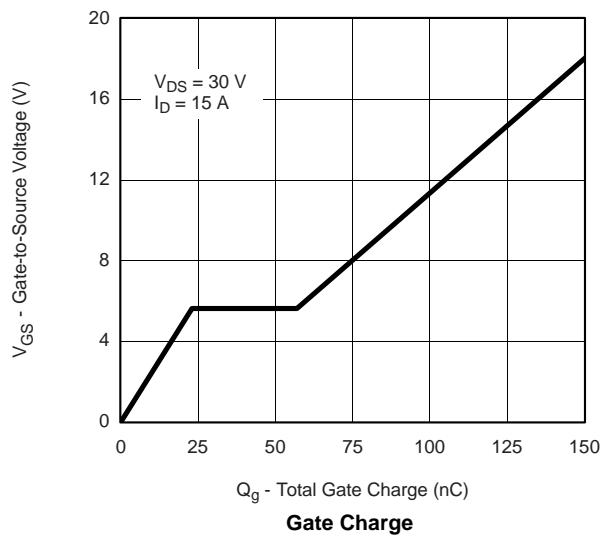
Transconductance



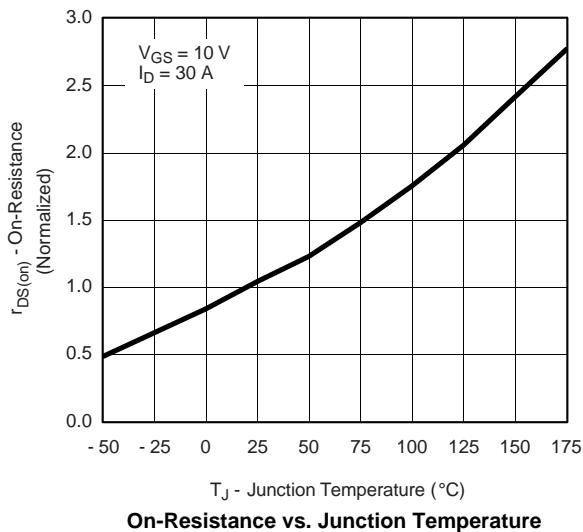
On-Resistance vs. Drain Current



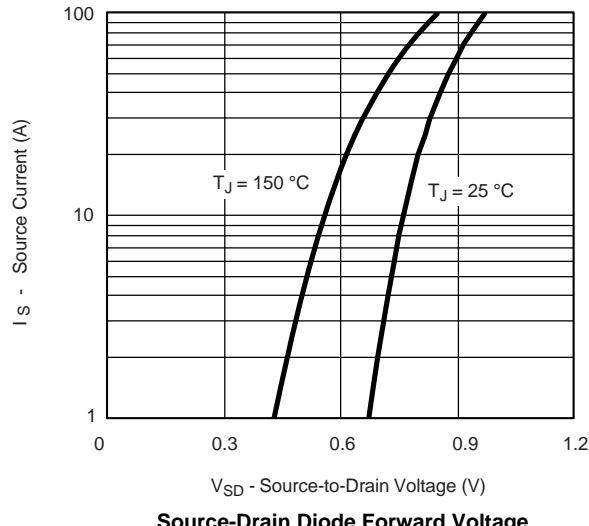
Capacitance



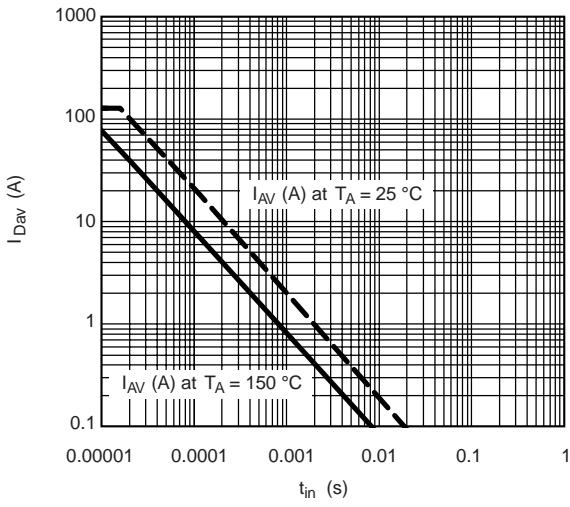
Gate Charge

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


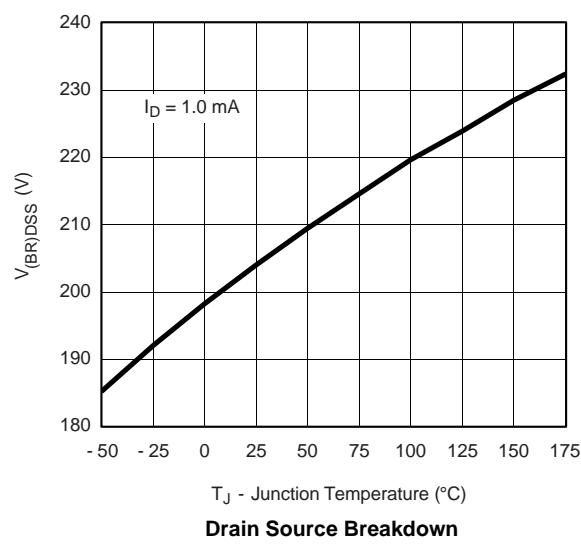
On-Resistance vs. Junction Temperature



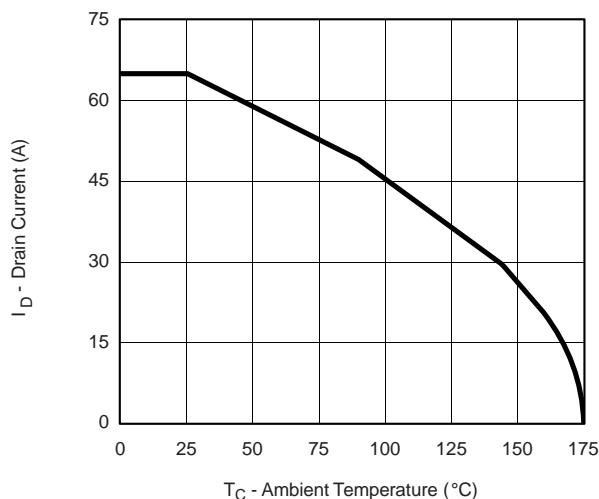
Source-Drain Diode Forward Voltage



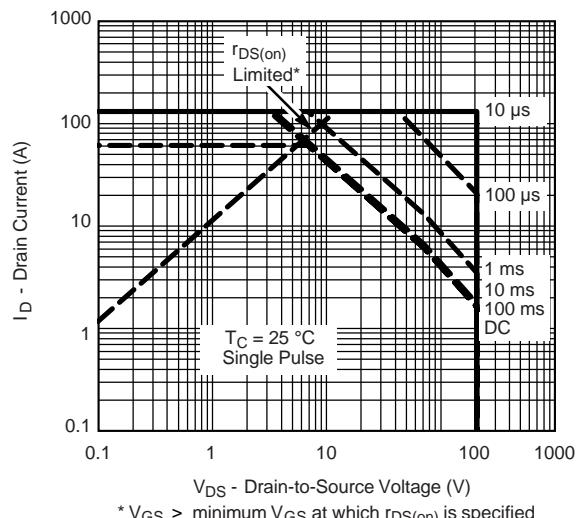
Avalanche Current vs. Time

Drain Source Breakdown
vs. Junction Temperature

THERMAL RATINGS

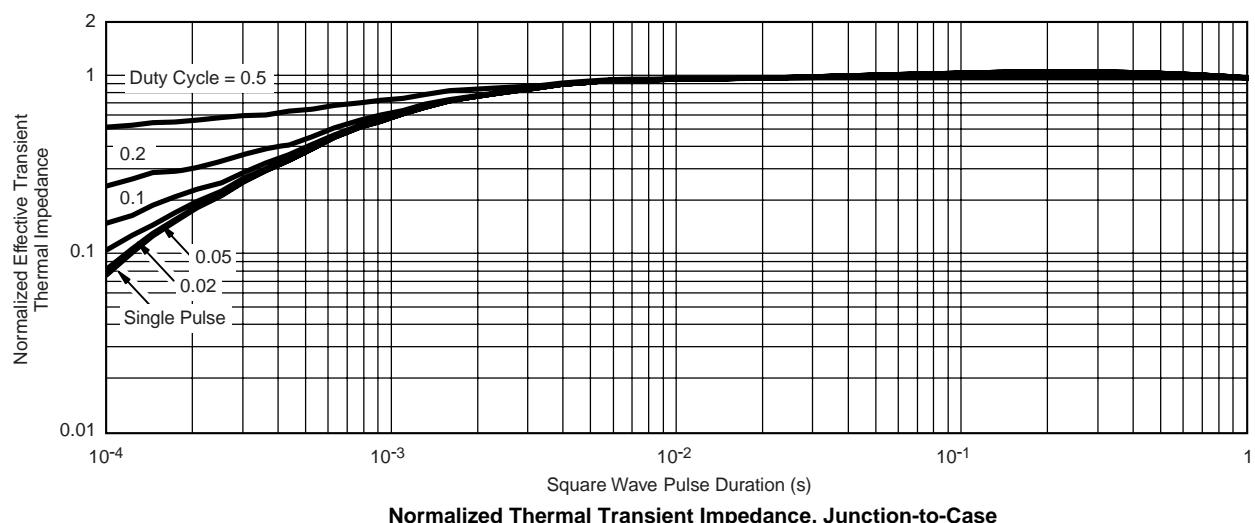


Maximum Avalanche and Drain Current
vs. Case Temperature



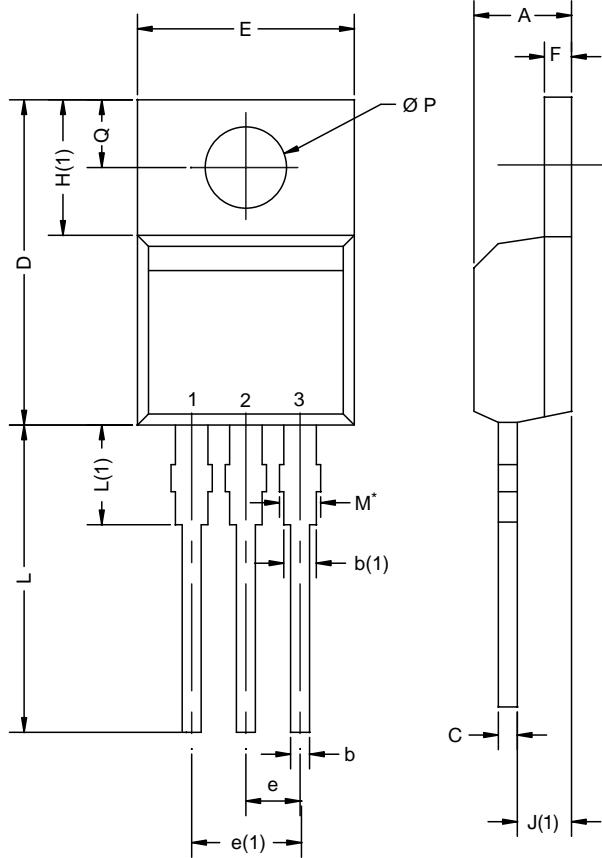
* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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